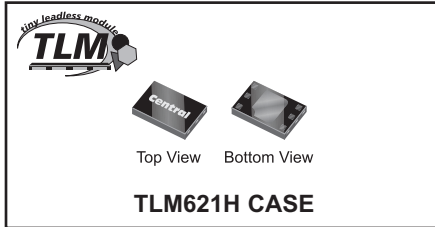


CTLDM7120-M621H

**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



www.centrasemi.com



• Device is **Halogen Free** by design

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$
Power Dissipation (Note 1)
Operating and Storage Junction Temperature
Thermal Resistance (Note 1)

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLDM7120-M621H is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(ON)}$ and Low Threshold Voltage.

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FEATURES:

- ESD protection up to 2kV
- Low $r_{DS(ON)}$ (0.25 Ω MAX @ $V_{GS}=1.5\text{V}$)
- High current ($I_D=1.0\text{A}$)
- Logic level compatibility

SYMBOL		UNITS
V_{DS}	20	V
V_{GS}	8.0	V
I_D	1.0	A
I_{DM}	4.0	A
P_D	1.6	W
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	75	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=8.0\text{V}, V_{DS}=0$			10	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0$			10	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=10\text{V}, I_D=1.0\text{mA}$	0.5		1.2	V
V_{SD}	$V_{GS}=0, I_S=1.0\text{A}$			1.1	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=0.5\text{A}$		0.075	0.10	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=0.5\text{A}$		0.10	0.14	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=0.1\text{A}$		0.17	0.25	Ω
$Q_g(\text{tot})$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=1.0\text{A}$		2.4		nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=1.0\text{A}$		0.25		nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=1.0\text{A}$		0.65		nC
g_{FS}	$V_{DS}=10\text{V}, I_D=0.5\text{A}$		4.2		S
C_{rSS}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
C_{iSS}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		220		pF
C_{OSS}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		120		pF
t_{on}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		25		ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		140		ns

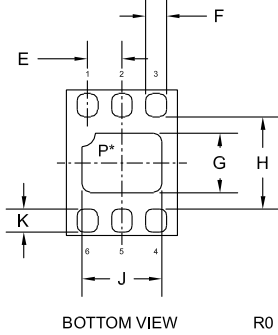
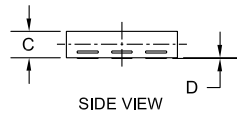
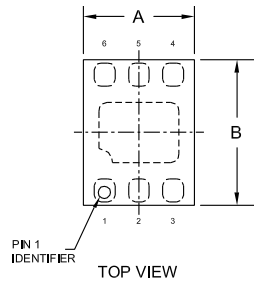
Notes: (1) Mounted on a 4-layer JEDEC test board with one thermal vias connecting the exposed thermal pad to the first buried plane. PCB was constructed as per JEDEC standards JESD51-5 and JESD51-7.

R3 (2-August 2011)

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TLM621H CASE - MECHANICAL OUTLINE

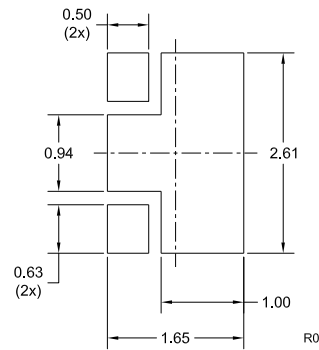


*Exposed pad P internally connected to pins 2, 3, 4, and 5.

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.053	0.065	1.35	1.65
B	0.073	0.085	1.85	2.15
C	0.012	0.016	0.30	0.40
D	0.000	0.002	0.00	0.05
E	0.020		0.50	
F	0.008	0.012	0.20	0.30
G	0.027	0.035	0.69	0.89
H	0.053	0.057	1.35	1.45
J	0.039	0.047	0.99	1.19
K	0.011	0.015	0.28	0.38

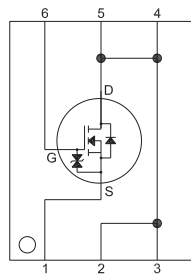
TLM621H (REV:R0)

OPTIONAL MOUNTING PADS
(Dimensions in mm)



For standard mounting refer to TLM621H Package Details

PIN CONFIGURATION



LEAD CODE:

- 1) Source
- 2) Drain
- 3) Drain
- 4) Drain
- 5) Drain
- 6) Gate

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